## NSN 5961-01-093-0111

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-093-0111 **Inclosure Material:** Glass and metal **Overall Length:** 0.786 inches **Terminal Length:** 0.125 inches **Overall Height:** 0.200 inches **Overall Width:** 0.210 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 40.0 collector to base voltage, dc all transistor and 40.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 1.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 2.5 watts small-signal input power, common-collector preset all transistor **Transfer Ratio:** 120.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** All semiconductor device diode junction pattern arrangement: pnp **Terminal Type And Quantity:** 14 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** 

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